



## Phase Control Thyristors (Stud Version), 200 A



TO-93 (TO-209AB)

### FEATURES

- Center amplifying gate
- International standard case TO-93 (TO-209AB)
- Glass-metal seal up to 1200 V
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

RoHS  
COMPLIANT

### PRIMARY CHARACTERISTICS

$I_{T(AV)}$	200 A
$V_{DRM}/V_{RRM}$	400 V, 800 V, 1200 V
$V_{TM}$	1.75 V
$I_{GT}$	150 mA
$T_J$	-40 °C to +125 °C
Package	TO-93 (TO-209AB)
Circuit configuration	Single SCR

### TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

### MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		200	A
	$T_C$	85	°C
$I_{T(RMS)}$		314	A
$I_{TSM}$	50 Hz	5000	A
	60 Hz	5230	
$I^2t$	50 Hz	125	kA <sup>2</sup> s
	60 Hz	114	
$V_{DRM}/V_{RRM}$		400 to 1200	V
$t_q$	Typical	100	μs
$T_J$		-40 to +125	°C

### ELECTRICAL SPECIFICATIONS

#### VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	$V_{DRM}/V_{RRM}$ , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	$V_{RSM}$ , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-ST180S	04	400	500	30
	08	800	900	
	12	1200	1300	

**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave		200	A
				85	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 76 °C case temperature		314	
Maximum peak, one-cycle non-repetitive surge current	$I_{TSM}$	t = 10 ms	No voltage reapplied	5000	A
		t = 8.3 ms	No voltage reapplied	5230	
		t = 10 ms	100 % $V_{RRM}$ reapplied	4200	
		t = 8.3 ms	100 % $V_{RRM}$ reapplied	4400	
Maximum $I^2t$ for fusing	$I^2t$	t = 10 ms	No voltage reapplied	125	kA <sup>2</sup> s
		t = 8.3 ms	No voltage reapplied	114	
		t = 10 ms	100 % $V_{RRM}$ reapplied	88	
		t = 8.3 ms	100 % $V_{RRM}$ reapplied	81	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied		1250	kA <sup>2</sup> √s
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$ ), $T_J = T_J$ maximum		1.08	V
High level value of threshold voltage	$V_{T(TO)2}$	(I $> \pi \times I_{T(AV)}$ ), $T_J = T_J$ maximum		1.14	
Low level value of on-state slope resistance	$r_{t1}$	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$ ), $T_J = T_J$ maximum		1.18	mΩ
High level value of on-state slope resistance	$r_{t2}$	(I $> \pi \times I_{T(AV)}$ ), $T_J = T_J$ maximum		1.14	
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 570$ A, $T_J = 125$ °C, $t_p = 10$ ms sine pulse		1.75	V
Maximum holding current	$I_H$	$T_J = T_J$ maximum, anode supply 12 V resistive load		600	mA
Maximum (typical) latching current	$I_L$			1000 (300)	

**SWITCHING**

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	$di/dt$	Gate drive 20 V, 20 Ω, $t_r \leq 1$ μs $T_J = T_J$ maximum, anode voltage $\leq 80$ % $V_{DRM}$	1000	A/μs
Typical delay time	$t_d$	Gate current 1 A, $di_g/dt = 1$ A/μs $V_d = 0.67$ % $V_{DRM}$ , $T_J = 25$ °C	1.0	μs
Typical turn-off time	$t_q$	$I_{TM} = 300$ A, $T_J = T_J$ maximum, $di/dt = 20$ A/μs, $V_R = 50$ V, $dV/dt = 20$ V/μs, gate 0 V 100 Ω, $t_p = 500$ μs	100	

**BLOCKING**

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	$dV/dt$	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/μs
Maximum peak reverse and off-state leakage current	$I_{RRM}$ , $I_{DRM}$	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	30	mA



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			TYP.	MAX.	
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms	10		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$	2.0		
Maximum peak positive gate current	$I_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms	3.0		A
Maximum peak positive gate voltage	$+V_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms	20		V
Maximum peak negative gate voltage	$-V_{GM}$		5.0		
DC gate current required to trigger	$I_{GT}$	$T_J = -40$ °C	180	-	mA
		$T_J = 25$ °C	90	150	
		$T_J = 125$ °C	40	-	
DC gate voltage required to trigger	$V_{GT}$	$T_J = -40$ °C	2.9	-	V
		$T_J = 25$ °C	1.8	3.0	
		$T_J = 125$ °C	1.2	-	
DC gate current not to trigger	$I_{GD}$	$T_J = T_J$ maximum	10		mA
DC gate voltage not to trigger	$V_{GD}$		0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	$T_J$		-40 to +125	°C
Maximum storage temperature range	$T_{Stg}$		-40 to +150	
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation	0.105	K/W
Maximum thermal resistance, case to heatsink	$R_{thC-hs}$	Mounting surface, smooth, flat and greased	0.04	
Mounting torque, $\pm 10$ %		Non-lubricated threads	31 (275)	N · m (lbf · in)
		Lubricated threads	24.5 (210)	
Approximate weight			280	g
Case style		See dimensions - link at the end of datasheet	TO-93 (TO-209AB)	

$\Delta R_{thJC}$ CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.015	0.012	$T_J = T_J$ maximum	K/W
120°	0.019	0.020		
90°	0.025	0.027		
60°	0.036	0.037		
30°	0.060	0.060		

**Note**

- The table above shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC

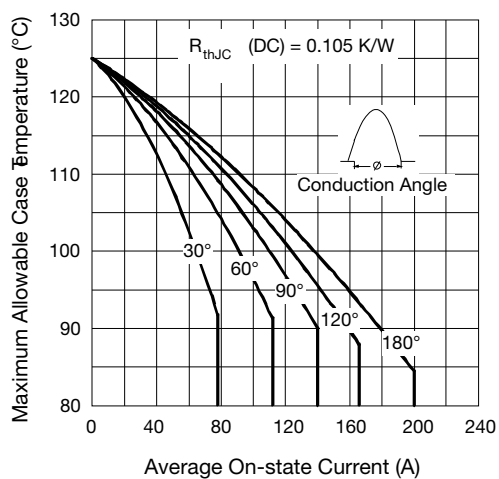


Fig. 1 - Current Ratings Characteristics

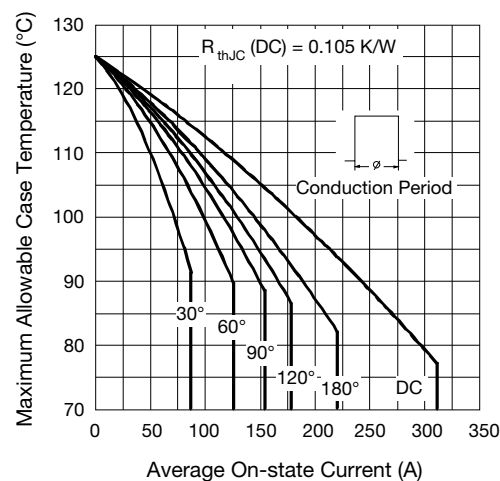


Fig. 2 - Current Ratings Characteristics

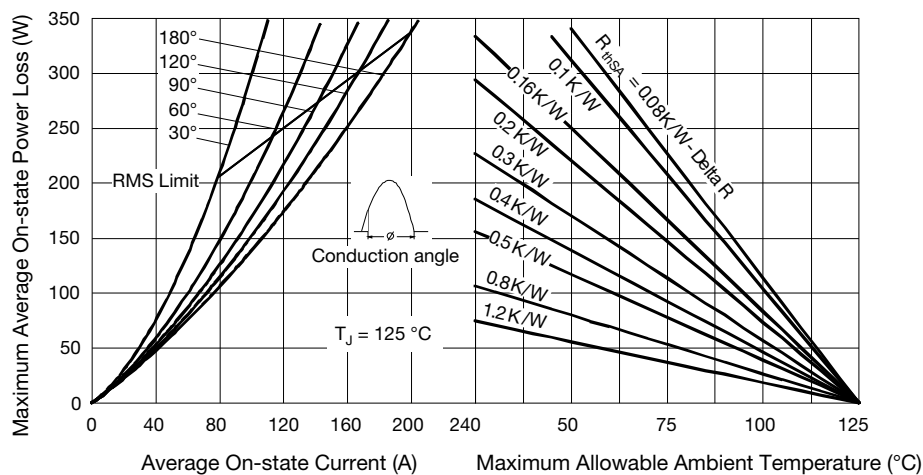


Fig. 3 - On-State Power Loss Characteristics

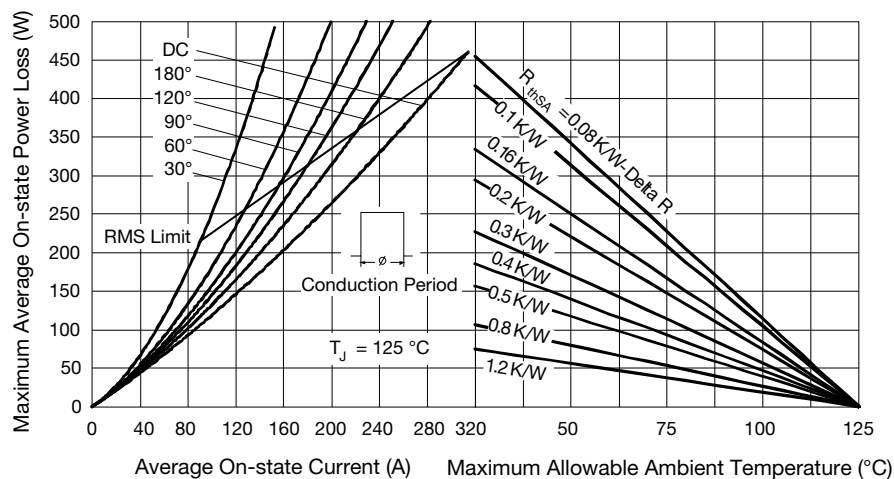


Fig. 4 - On-State Power Loss Characteristics

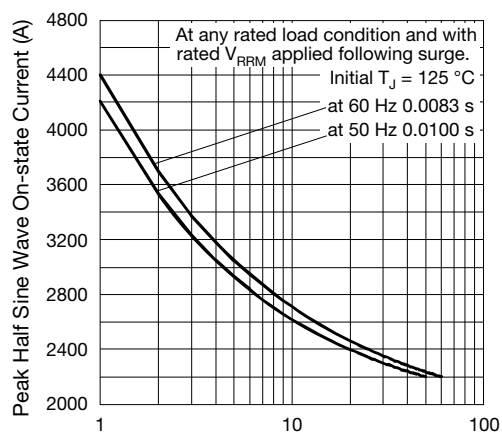


Fig. 5 - Maximum Non-Repetitive Surge Current

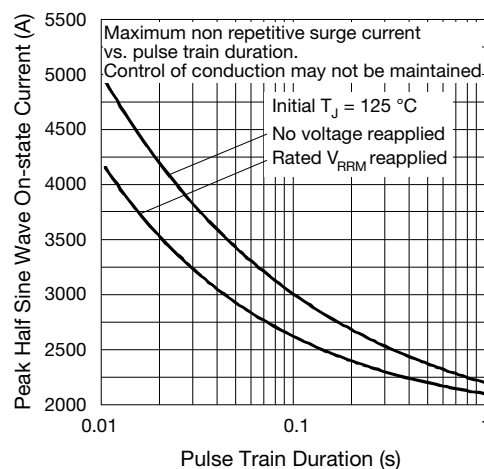


Fig. 6 - Maximum Non-Repetitive Surge Current

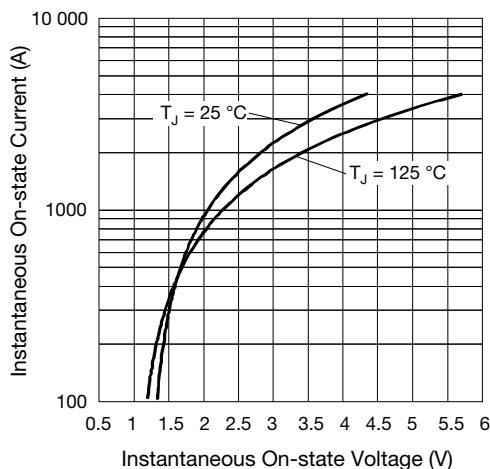
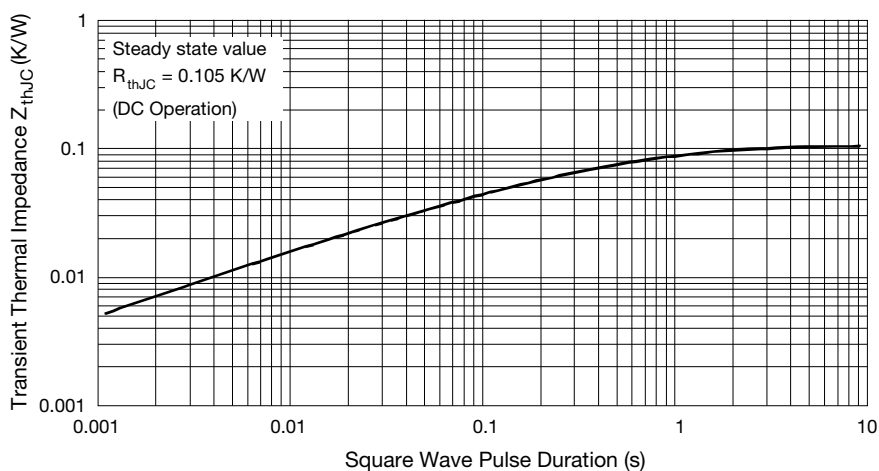


Fig. 7 - On-State Voltage Drop Characteristics

Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

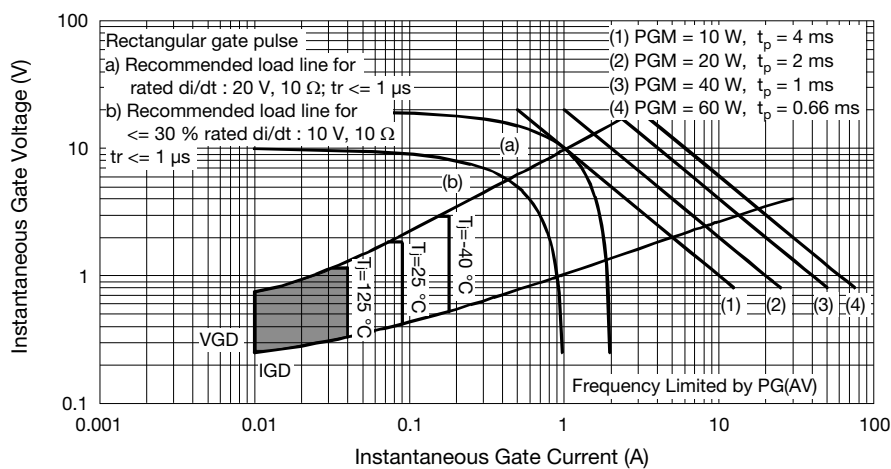


Fig. 9 - Gate Characteristics

## ORDERING INFORMATION TABLE

Device code	VS-	ST	18	0	S	20	P	0	V	PbF
	1	2	3	4	5	6	7	8	9	10
1	Vishay Semiconductors product									
2	Thyristor									
3	Essential part number									
4	0 = converter grade									
5	S = compression bonding stud									
6	Voltage code x 100 = $V_{RRM}$ (see Voltage Ratings table)									
7	P = stud base 3/4"-16UNF2A threads									
8	0 = eyelet terminals (gate and auxiliary cathode leads) 1 = fast-on terminals (gate and auxiliary cathode leads)									
9	V = glass-metal seal (only up to 1200 V)									
10	None = standard production PbF = lead (Pb)-free									

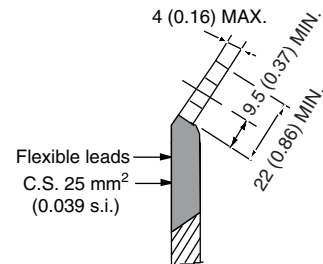
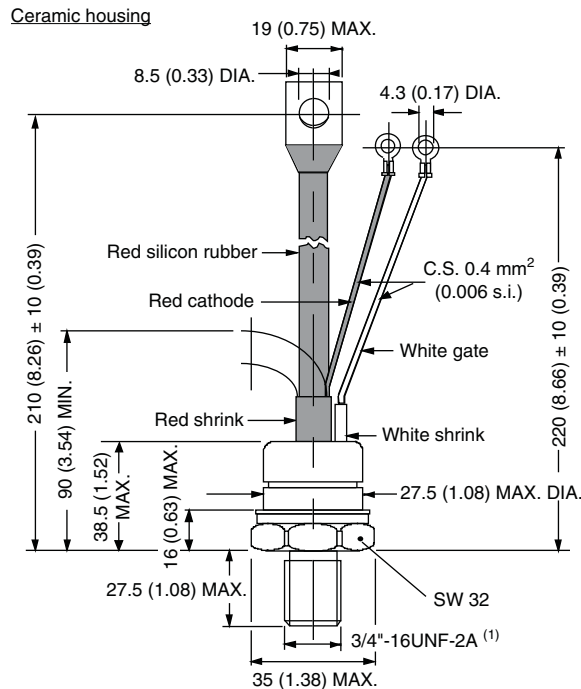
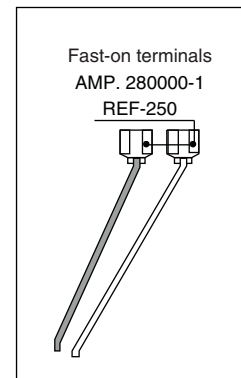
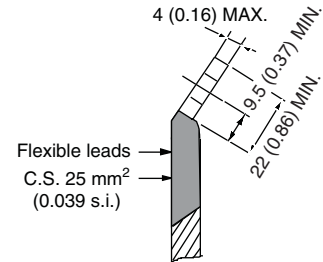
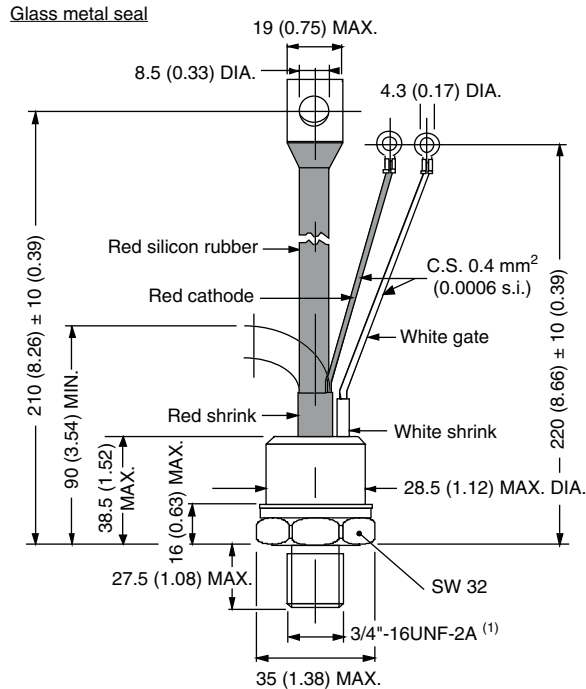
## LINKS TO RELATED DOCUMENTS

Dimensions

[www.vishay.com/doc?95082](http://www.vishay.com/doc?95082)

### TO-209AB (TO-93)

#### DIMENSIONS in millimeters (inches)



#### Note

(1) For metric device: M16 x 1.5 - length 21 (0.83) maximum



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